

Timo Schumann

List of Publications by Year in descending order

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39
papers

1,524
citations

361413

20
h-index

330143

37
g-index

39
all docs

39
docs citations

39
times ranked

2397
citing authors

#	ARTICLE	IF	CITATIONS
19	Surface passivation of the Dirac semimetal Cd_3As_2 . <i>Physical Review Letters</i> , 2017, 118, 166101.	2.4	16
20	Controlled synthesis and characterization of multilayer graphene films on the C_60 face of silicon carbide. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600721.	1.8	14
21	HAADF-STEM Study of MBE-Grown Dirac Semimetal Cd_3As_2 . <i>Microscopy and Microanalysis</i> , 2017, 23, 1480-1481.	0.4	0
22	Negative magnetoresistance due to conductivity fluctuations in films of the topological semimetal Cd_3As_2 . <i>Physical Review Letters</i> , 2017, 118, 166101.	3.2	68
23	Structure and optical band gaps of $(Ba,Sr)SnO_3$ films grown by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016, 34, .	2.1	45
24	Conduction band edge effective mass of La-doped $BaSnO_3$. <i>Applied Physics Letters</i> , 2016, 108, .	3.3	39
25	Molecular beam epitaxy of Cd_3As_2 on a III-V substrate. <i>APL Materials</i> , 2016, 4, .	5.1	68
26	High-mobility $BaSnO_3$ grown by oxide molecular beam epitaxy. <i>APL Materials</i> , 2016, 4, .	5.1	181
27	Synthesis of quasi-free-standing bilayer graphene nanoribbons on SiC surfaces. <i>Nature Communications</i> , 2015, 6, 7632.	12.8	42
28	Synthesis of atomically thin hexagonal boron nitride films on nickel foils by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	81
29	The impact of substrate selection for the controlled growth of graphene by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2015, 425, 274-278.	1.5	13
30	Molecular beam epitaxy of graphene on ultra-smooth nickel: growth mode and substrate interactions. <i>New Journal of Physics</i> , 2014, 16, 093055.	2.9	16
31	Effect of buffer layer coupling on the lattice parameter of epitaxial graphene on SiC(0001). <i>Physical Review B</i> , 2014, 90, .	3.2	36
32	Acousto-electric transport in epitaxial monolayer graphene on SiC. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	44
33	Mono- and few-layer nanocrystalline graphene grown on $Al_2O_3(0001)$ by molecular beam epitaxy. <i>Carbon</i> , 2013, 56, 339-350.	10.3	54
34	Formation of high-quality quasi-free-standing bilayer graphene on SiC(0001) by oxygen intercalation upon annealing in air. <i>Carbon</i> , 2013, 52, 83-89.	10.3	104
35	Structural investigation of nanocrystalline graphene grown on $(6\sqrt{3}\text{Å} \times 6\sqrt{3}\text{Å})R30^\circ$ -reconstructed SiC surfaces by molecular beam epitaxy. <i>New Journal of Physics</i> , 2013, 15, 123034.	2.9	16
36	Photoluminescence and Raman scattering studies of GaN nanowires obtained by top-down and bottom-up approaches. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1408, 29.	0.1	2

#	ARTICLE	IF	CITATIONS
37	Influence of the adatom diffusion on selective growth of GaN nanowire regular arrays. Applied Physics Letters, 2011, 98, .	3.3	58
38	Cathodoluminescence spectroscopy on selectively grown GaN nanowires. Proceedings of SPIE, 2011, , .	0.8	2
39	Selective-area catalyst-free MBE growth of GaN nanowires using a patterned oxide layer. Nanotechnology, 2011, 22, 095603.	2.6	91